

NIC9N05TS1, NIC9N05ATS1

Protected Power MOSFET

2.6 A, 52 V, N-Channel, Logic Level,
Clamped MOSFET w/ ESD Protection

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

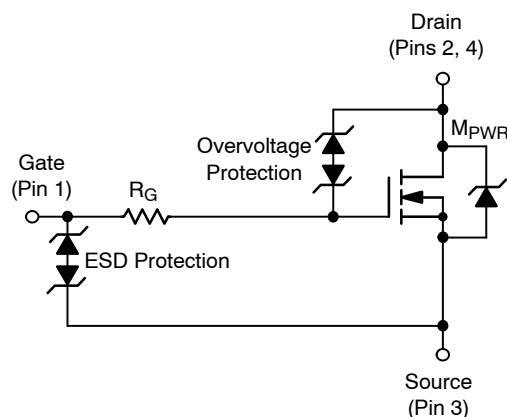
Rating	Symbol	Value	Unit
Drain-to-Source Voltage Internally Clamped	V_{DSS}	52–59	V
Gate-to-Source Voltage – Continuous	V_{GS}	± 15	V
Operating and Storage Temperature Range	T_J, T_{stg}	–55 to 150	$^\circ\text{C}$
Electro-Static Discharge Capability (HBM) (MM)	ESD	5000 500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified) (Note 1)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage (V _{GS} = 0 V, I _D = 1.0 mA, T _J = 25°C)	V _{(BR)DSS}	52	55	59	V
Zero Gate Voltage Drain Current (V _{DS} = 40 V, V _{GS} = 0 V)	I _{DSS}			10	μA
Gate-Body Leakage Current (V _{GS} = ±8 V, V _{DS} = 0 V) (V _{GS} = ±14 V, V _{DS} = 0 V)	I _{GSS}		±22	±10	μA
ON CHARACTERISTICS					
Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 100 μA)	V _{GS(th)}	1.3	1.75	2.5	V
Static Drain-to-Source On-Resistance (V _{GS} = 3.5 V, I _D = 0.6 A) (V _{GS} = 4.0 V, I _D = 1.5 A) (V _{GS} = 10 V, I _D = 2.6 A)	R _{DS(on)}		190 165 107	380 200 125	mΩ
SOURCE-DRAIN DIODE CHARACTERISTICS					
Forward On-Voltage	I _S = 2.6 A, V _{GS} = 0 V I _S = 2.6 A, V _{GS} = 0 V, T _J = 125°C	V _{SD}		0.81 0.66	1.5 V

1. Wafers tested prior to sawing.

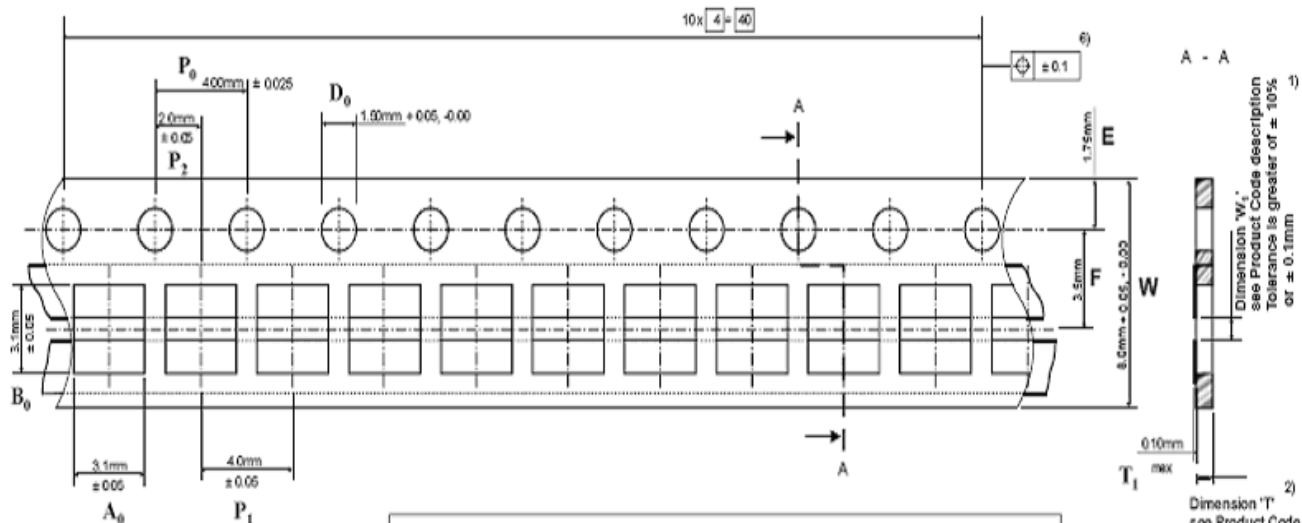
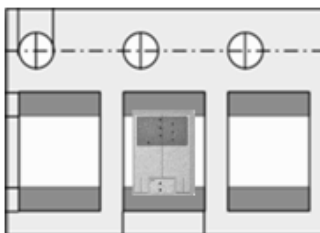
ORDERING INFORMATION

Device	Shipping
NIC9N05TS1	5000 / Reel
NIC9N05ATS1	5000 / Reel

NIC9N05TS1, NIC9N05ATS1

Layout view of the die in reel

Orientation A



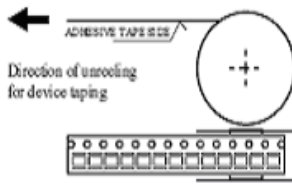
- NOTES**
1. W₁ is specified in the product description and is typically 50% of the component length as laid across the tape width. Tolerance of W₁ is ± 0.1mm or ± 10%, whichever is the greater.
 2. T₁ is specified in the product description and is always greater than the thickness of the component. Tolerance of T₁ is ± 10%.
 3. Total thickness of the tape is T = T₁.
 4. Main tape body volume conductivity 10⁴ to 10⁶ ohms per square. Material modified HIPS or ABS.
 5. Adhesive tape surface resistivity 10¹² ohms per square. Material Nibo SWT10 unless otherwise specified.
 6. Cumulative tolerance for 40 consecutive pitches is ± 0.1mm.

Product code description

S184T-W₁

T = .33, .45, .6, .7, or .85 (mm), as ordered
W₁ = 0.7 to 1.2 (mm) in increments of 0.1, as ordered

For example
S184 7-0.8
Type S184, T=0.7mm, W₁=0.7mm.



Change T0000 Drawing errors corrected - no change to dimensions or tolerances			
Property data Company confidential All rights reserved	Drawing according to ISO 9015 General tolerances ± 0.05mm	Scale 10:1	
		Date: 06/02/05	
		Name: Ken Ball	
		TEMPO ELECTRONICS www.surftape.com	
		S184 type	
		ADHESIVE BACKED PUNCHED PLASTIC CARRIER TAPE	
		SURFTAPE®	

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